# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





30 V, Dual N-channel Trench MOSFET 15 April 2016

Product data sheet

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor		·					,
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	-	0.95	А
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C		-	211	252	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



30 V, Dual N-channel Trench MOSFET

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

### 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PMGD175XNE	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMGD175XNE	LU%

[1] % = placeholder for manufacturing site code

30 V, Dual N-channel Trench MOSFET

### 8. Limiting values

#### Table 5.Limiting values

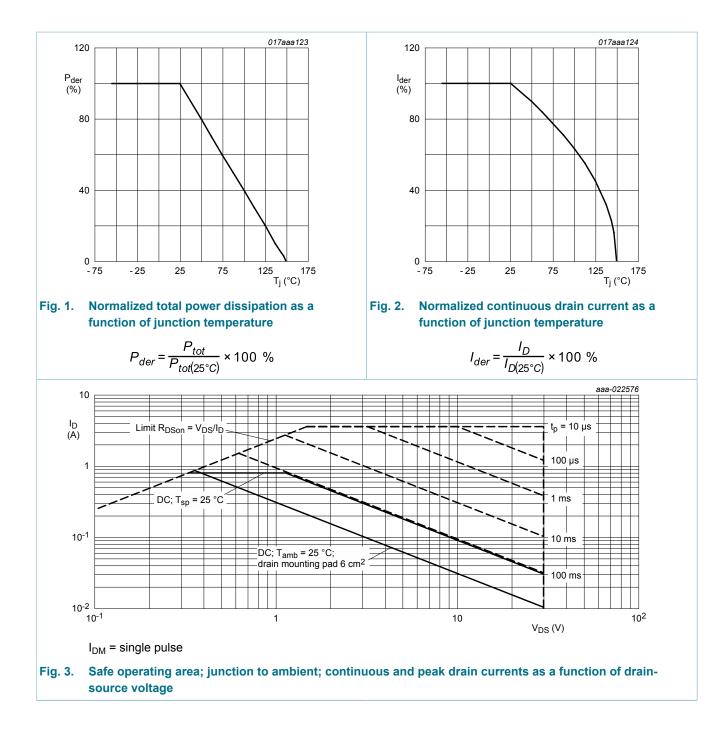
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C; t ≤ 5 s	[1]	-	0.95	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	0.87	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	4	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	m₩
			[1]	-	310	mΨ
		T <sub>sp</sub> = 25 °C		-	905	mW
Per device					·	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	390	m₩
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.31	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 30 V, Dual N-channel Trench MOSFET



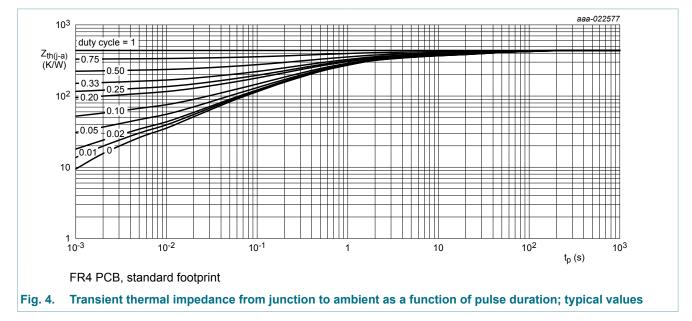
#### 30 V, Dual N-channel Trench MOSFET

#### **Thermal characteristics** 9.

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor	·	·					
R <sub>th(j-a)</sub>	thermal resistance	in free air [1] [2]	[1]	-	417	480	K/W
from junction to ambient	-		[2]	-	352	405	K/W
	ampient	in free air; t ≤ 5 s	[2]	-	295	340	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	120	138	K/W
Per device		1					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	320	K/W

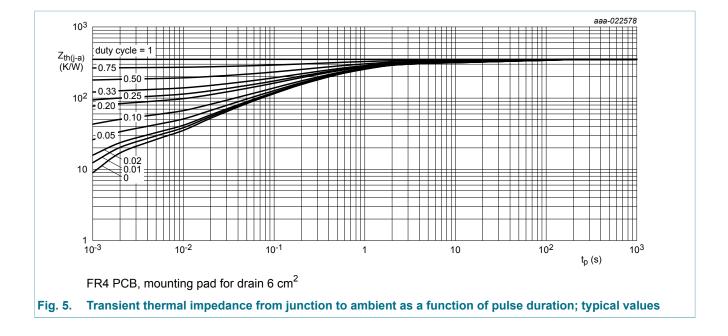
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



### PMGD175XNE

#### 30 V, Dual N-channel Trench MOSFET



30 V, Dual N-channel Trench MOSFET

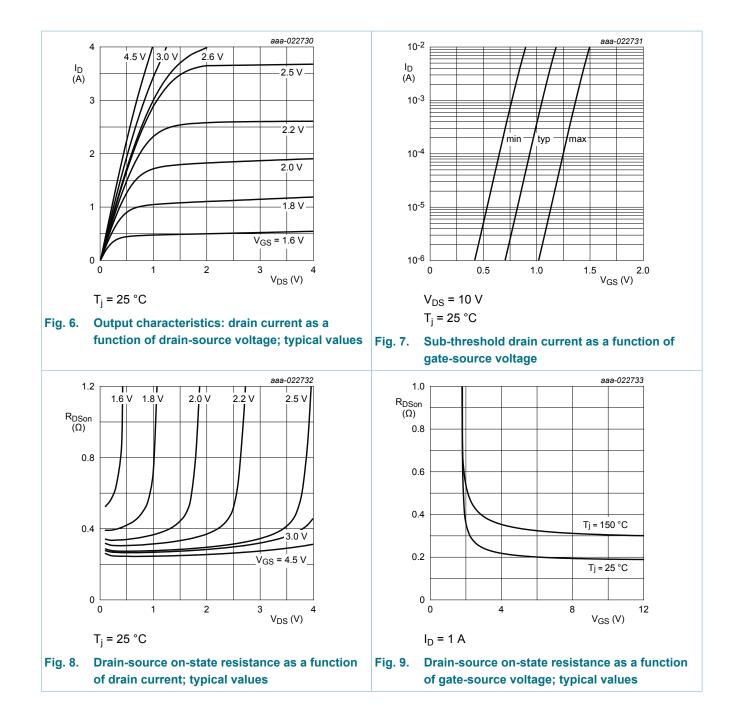
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.75	1	1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	5	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-5	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C	-	211	252	mΩ
resist	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 150 °C	-	344	411	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 0.8 A; T <sub>j</sub> = 25 °C	-	267	319	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 0.9 A; T <sub>j</sub> = 25 °C	-	3.5	-	S
Dynamic ch	aracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 15 V; I <sub>D</sub> = 0.9 A; V <sub>GS</sub> = 4.5 V;	-	1.05	1.65	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.15	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.27	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	81	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \ ^{\circ}C$	-	13	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	9	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; I <sub>D</sub> = 0.9 A; V <sub>GS</sub> = 4.5 V;	-	7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	17	-	ns
t <sub>f</sub>	fall time	1	-	6	-	ns
Source-drai	in diode (per transistor)			- 1		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 0.3 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.7	1.2	V

PMGD175XNE

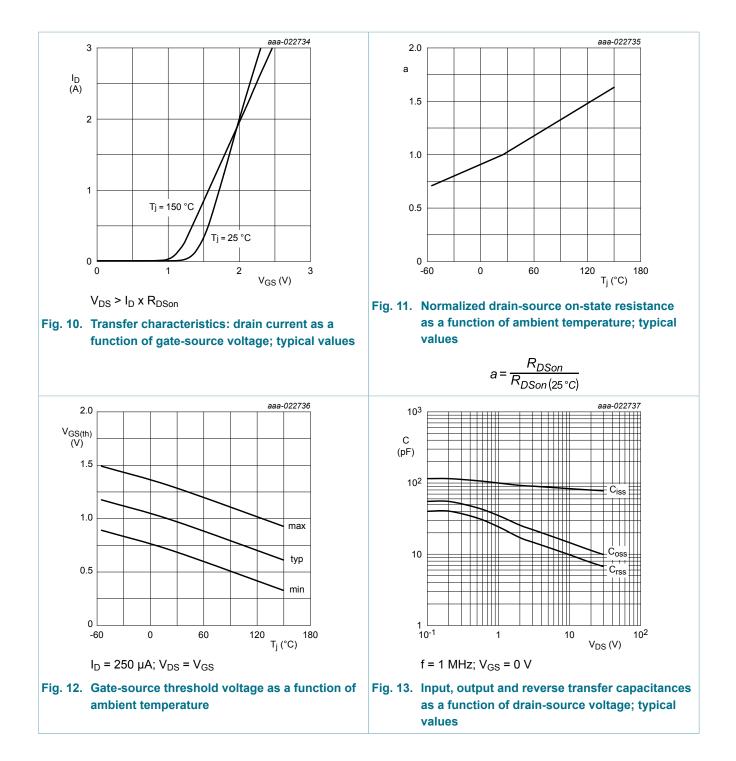
### PMGD175XNE

#### 30 V, Dual N-channel Trench MOSFET



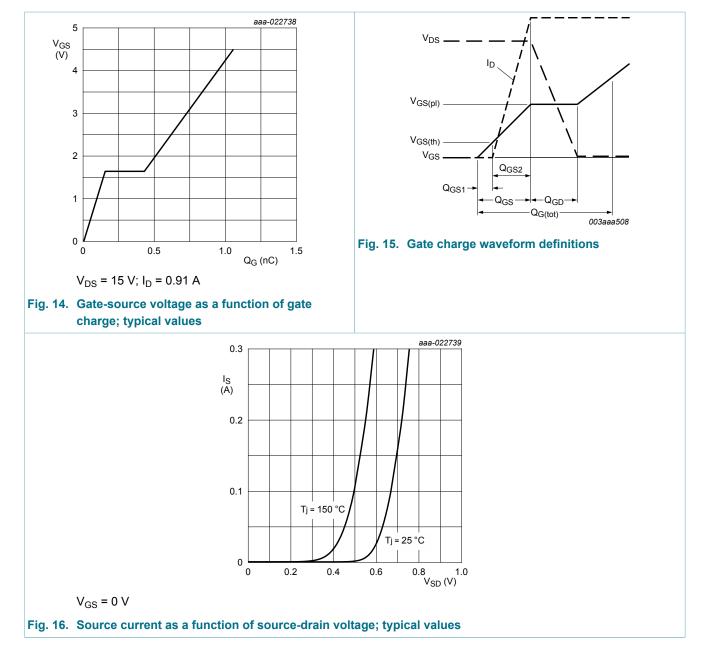
### PMGD175XNE

#### 30 V, Dual N-channel Trench MOSFET

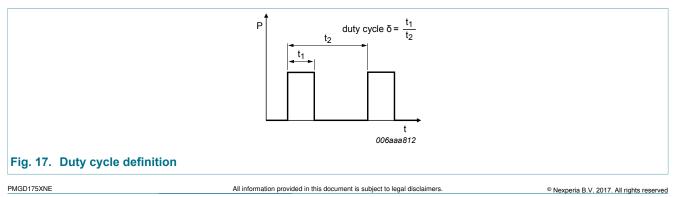


### PMGD175XNE

#### 30 V, Dual N-channel Trench MOSFET

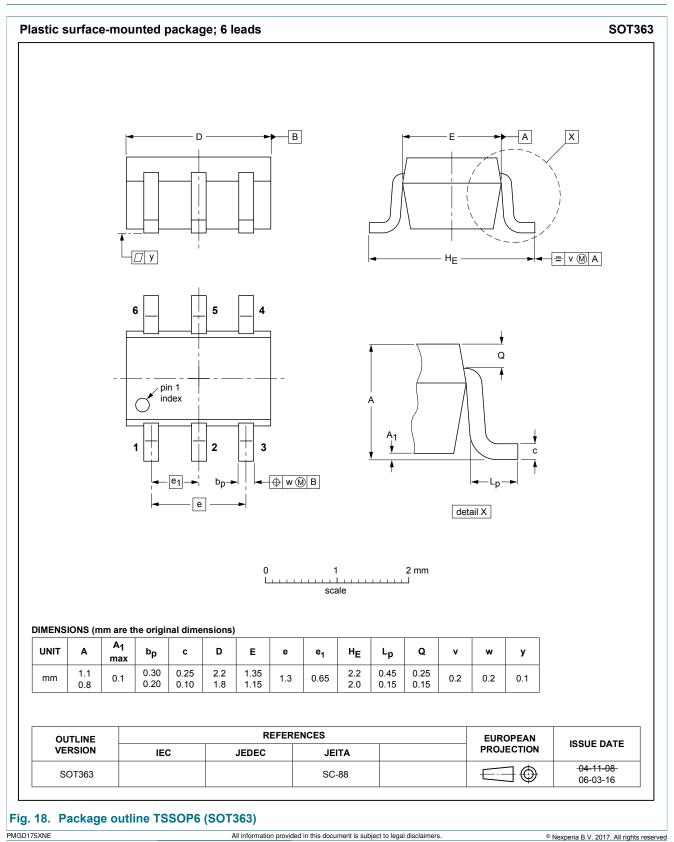


### **11. Test information**



#### 30 V, Dual N-channel Trench MOSFET

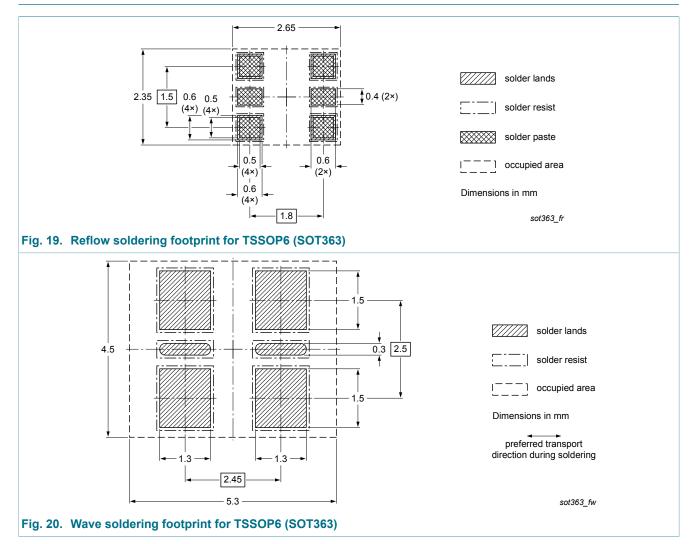
### 12. Package outline



Product data sheet

#### 30 V, Dual N-channel Trench MOSFET

### 13. Soldering



#### 30 V, Dual N-channel Trench MOSFET

### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMGD175XNE v.1	20160415	Product data sheet	-	-		

#### 30 V, Dual N-channel Trench MOSFET

#### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

#### 15.2 Definitions

**Preview** — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. Nexperia takes no responsibility for the content in this document if provided by an information source outside of Nexperia.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

**Right to make changes** — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia and its suppliers accept no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

#### Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nexperia.com/profile/terms">http://www.nexperia.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the

#### 30 V, Dual N-channel Trench MOSFET

grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Nexperia product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications. standard warranty and Nexperia's

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 30 V, Dual N-channel Trench MOSFET

### 16. Contents

1	General description1
2	Features and benefits1
3	Applications1
4	Quick reference data 1
5	Pinning information2
6	Ordering information2
7	Marking2
8	Limiting values3
9	Thermal characteristics5
10	Characteristics7
11	Test information10
12	Package outline 11
13	Soldering 12
14	Revision history13
15	Legal information14
15.1	Data sheet status 14
15.2	Definitions14
15.3	Disclaimers14
15.4	Trademarks 15

#### © Nexperia B.V. 2017. All rights reserved

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 15 April 2016